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December 2013

FQP6N90C / FQPF6N90C

N-Channel QFET® MOSFET

900 V, 6.0 A, 2.3 Ω

Description

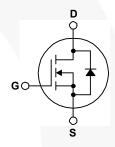
This N-Channel enhancement mode power MOSFET is • 6.0 A, 900 V, $R_{DS(on)}$ = 2.3 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 30 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 11 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 3.0 A$







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP6N90C	FQPF6N90C	Unit
V _{DSS}	Drain-Source Voltage		900		V
I _D	Drain Current - Continuous (T _C = 25°C)		6	6 *	Α
	- Continuous (T _C = 100°C)	F	3.8	3.8 *	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	24	24 *	Α
V _{GSS}	Gate-Source Voltage		±	30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		650		mJ
I _{AR}	Avalanche Current		6		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		16.7		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_{D}	Power Dissipation (T _C = 25°C)		167	56	W
	- Derate above 25°C		1.43	0.48	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		3	00	°C

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP6N90C	FQPF6N90C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.75	2.25	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP6N90C	FQP6N90C	TO-220	Tube	N/A	N/A	50 units
FQPF6N90C	FQPF6N90C	TO-220F	Tube	N/A	N/A	50 units

Test Conditions

Min. Typ.

Max.

Unit

Electrical Characteristics T_C = 25°C unless otherwise noted

Parameter

0,	1 dramotor	100t Conditions		. 7 6.	maxi	0
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	900			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		1.07		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 900 V, V _{GS} = 0 V			10	μΑ
	Zero Gate voltage Drain Current	V _{DS} = 720 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
Vocab	Gate Threshold Voltage	Vpc = Vcc	3.0		5.0	V

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3 A		1.93	2.3	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_{D} = 3 \text{ A}$		5.5		S

Dynamic Characteristics

Symbol

C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	 1360	1770	pF
Coss	Output Capacitance	f = 1.0 MHz	 110	145	pF
C _{rss}	Reverse Transfer Capacitance		 11	15	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 450 V, I _D = 6 A,		35	80	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		90	190	ns
t _{d(off)}	Turn-Off Delay Time			55	120	ns
t _f	Turn-Off Fall Time	(Note 4)		60	130	ns
Q_g	Total Gate Charge	V _{DS} = 720 V, I _D = 6 A,		30	40	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V	/	9.0		nC
Q_{gd}	Gate-Drain Charge	(Note 4)	-	12		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				6.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				24	Α
V_{SD}	Drain-Source Diode Forward Voltage V _{GS} = 0 V, I _S = 6 A)	1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 6 \text{ A,}$		630	//	ns
Q _{rr}	Reverse Recovery Charge $dI_F / dt = 100 \text{ A/}\mu\text{s}$			6.9		μС

- **Notes:**1. Repetitive rating : pulse-width limited by maximum junction temperature.
 2. L = 34 mH, I_{AS} = 6 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
 3. $I_{SD} \le 6$ A, di/dt ≤ 200 A/ μ s , $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.
 4. Essentially independent of operating temperature.

Typical Characteristics

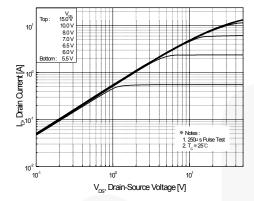


Figure 1. On-Region Characteristics

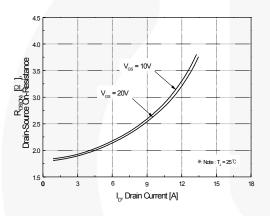


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

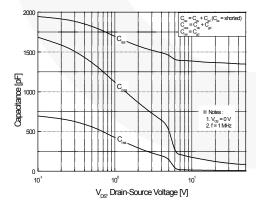


Figure 5. Capacitance Characteristics

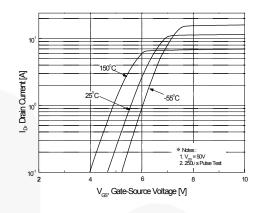


Figure 2. Transfer Characteristics

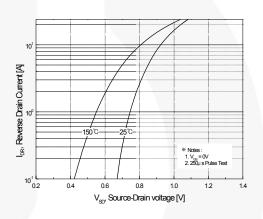


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

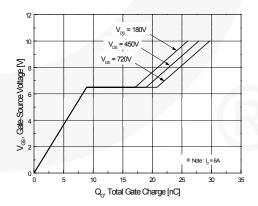


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

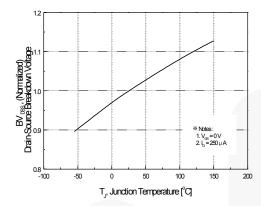


Figure 7. Breakdown Voltage Variation vs Temperature

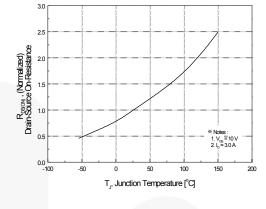


Figure 8. On-Resistance Variation vs Temperature

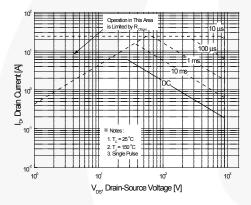


Figure 9-1. Maximum Safe Operating Area for FQP6N90C

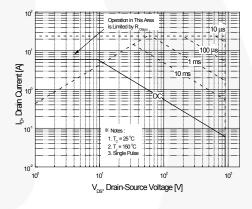


Figure 9-2. Maximum Safe Operating Area for FQPF6N90C

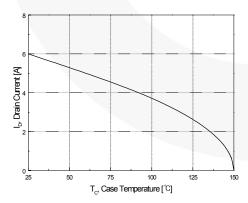


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

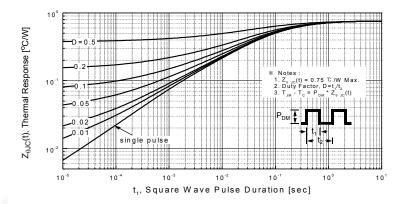


Figure 11-1. Transient Thermal Response Curve for FQP6N90C

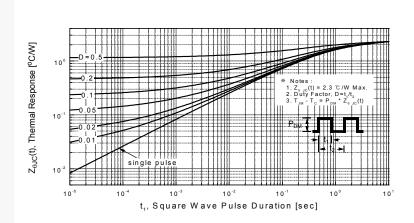


Figure 11-2. Transient Thermal Response Curve for FQPF6N90C

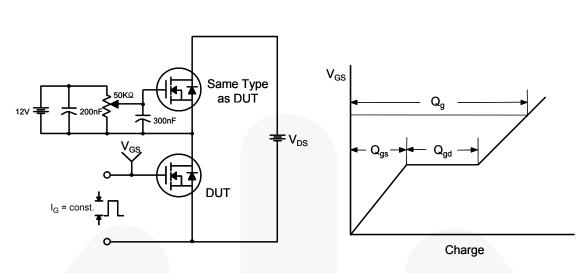


Figure 12. Gate Charge Test Circuit & Waveform

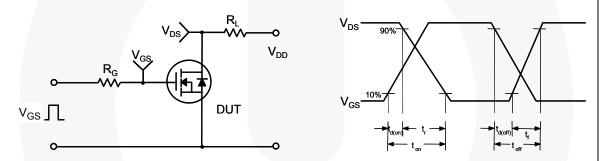


Figure 13. Resistive Switching Test Circuit & Waveforms

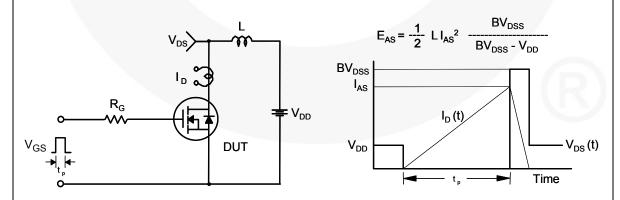
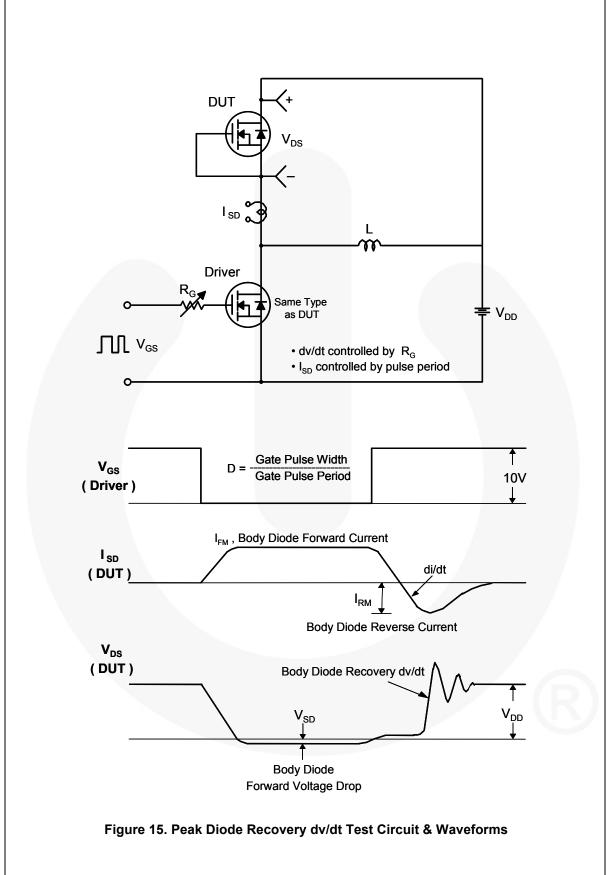


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

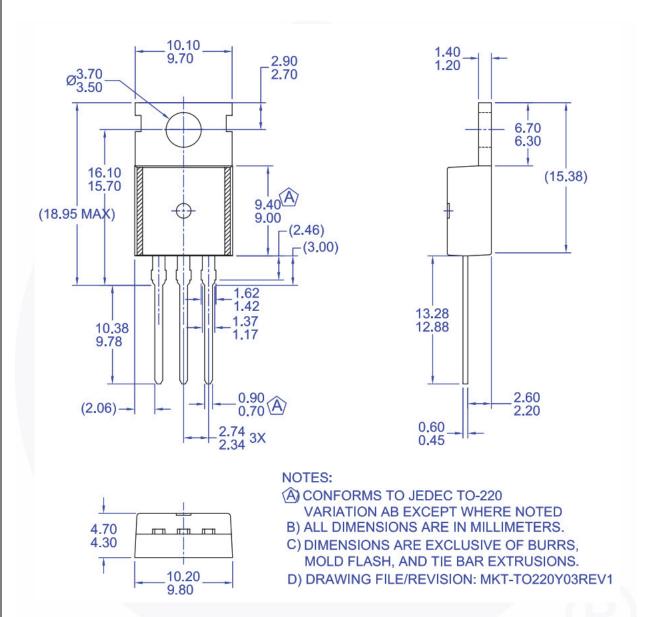


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

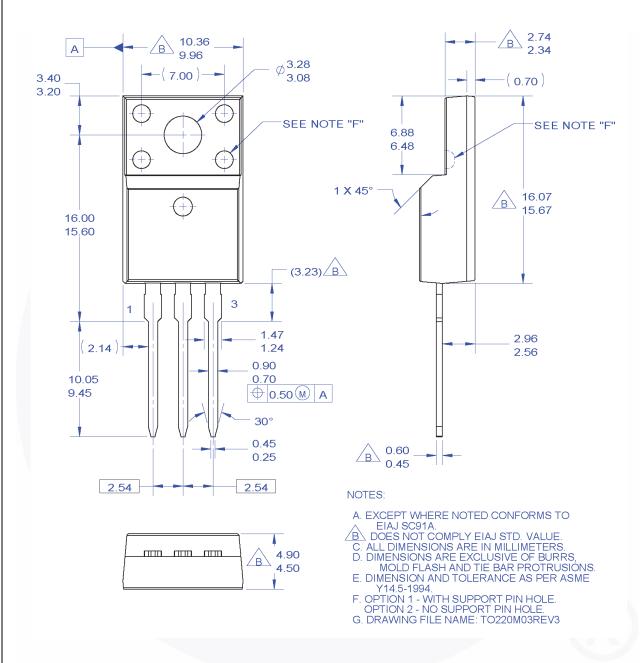


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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